

SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

Abstract of Disclosure

A method for fabricating a semiconductor device includes the steps of first forming a magnetic tunneling junction (MTJ) stack on a substrate, forming an etch stop layer on the MTJ stack, forming a first spin orbit torque (SOT) layer on the etch stop layer, and then patterning the first SOT layer, the etch stop layer, and the MTJ stack to form a MTJ.

Figure 1